

Amendments to the Claims

1. (currently amended) A method for manufacturing a semiconductor device comprising:
forming an N region and P region on a substrate, forming wiring so as to connect one or both of
~~these~~ the N and P regions; and
performing a processing step on a semiconductor substrate on which the upper surface of said
wiring is exposed using a liquid applied to said semiconductor substrate and a light source
radiating light onto said semiconductor substrate,
wherein said processing step is performed in a state in which the wavelength of light radiated
onto said semiconductor substrate is 500 nm to less than 1 μm , and
wherein said processing step is a cleaning step performed during, before or after a step that
includes chemical mechanical polishing (CMP) for forming said wiring.
2. (original) A method according to claim 1, wherein said processing step is performed in a
state in which said semiconductor substrate is grounded.
3. (canceled).
4. (withdrawn) A processing system comprising a processing unit that processes a semiconductor
substrate using a liquid and a light source.
5. (withdrawn) A processing system according to claim 4, wherein said light source radiates light
having a wavelength of 500nm to less than 1 μm onto said processing unit.

6. (withdrawn) A processing system according to claim 4, wherein said processing unit provided with a rotating section that holds and rotates a semiconductor substrate, and a liquid supply section that supplies liquid to said semiconductor substrate, and said rotating section being grounded.

7. (withdrawn) A processing system according to claim 5, wherein said processing unit provided with a rotating section that holds and rotates a semiconductor substrate, and a liquid supply section that supplies liquid to said semiconductor substrate, and said rotating section being grounded.

8. (withdrawn) A semiconductor device comprising:
a first N region and a P region formed on a substrate;
wiring formed so as to connect either or both of these N and P regions; and
the upper surface of said wiring being exposed to light,
wherein a second N region is formed independent of said first N region on said substrate.

9. (withdrawn) A semiconductor device according to claim 8, wherein the total surface area of said first N region and said second N region is 100 to 1/100 times the total surface area of said P region.

10. (withdrawn) A semiconductor device according to claim 8, wherein said second N region is formed at the periphery of said substrate.

11. (withdrawn) A semiconductor device according to claim 8, wherein said wiring has any one of Cu, Al and W as its main component.

12. (canceled).